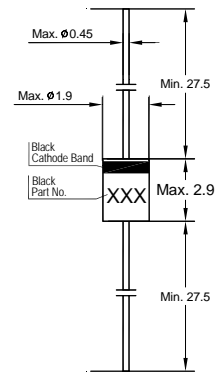


MA700B

SILICON SCHOTTKY BARRIER DIODE



Glass Case DO-34
Dimensions in mm

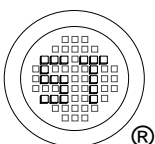
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	20	V
Power Dissipation	P_{tot}	400 ¹⁾	mW
Peak Surge Current (Single Cycle 60 Hz Sine Wave)	I_{FSM}	15	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_S	- 55 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 90\text{ mA}$	V_F	-	1	V
Reverse Leakage Current at $V_R = 20\text{ V}$	I_R	-	30	μA
Junction Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	50	-	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$ to 200 mA , recover to $0.1 I_R$	t_{rr}	10	-	ns



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company
listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 25/06/2007